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Information Disclosure Statement by Applicant						Applicant: Bernard Aspar et al			
(Use several sheets if necessary)						Filed: Group: Unassigned			
<b>U.S. Patent Documents</b>									
Init.		Document No.	Date	Name	Class	Subclass	Filing Date		
dm		5,863,830	1/99	Bruehl et al					
dm		6,821,376	11/04	Rayssac					
dm		6,204,079	3/01	Aspar et al					
dm		6,232,136	5/01	Zavracky et al					
dm		5,618,739	4/97	Takahashi et al					
dm		6,521,511	2/03	Inoue et al					
dm		6,506,664	1/03	Beyne					
<b>Foreign Documents</b>									
								Translation	
Init.		Document No.	Date	Country	Class	Subclass	Yes	No	
dm		0703 609 A1	3/96	EP			X		
dm		2 796 491	7/99	FR			X		
dm		0 977 252 A1	2/00	EP			X		
dm		0 924 769 A1	6/99	EP				X	
dm		1 041 624 A1	10/00	EP				X	
<b>Other Documents (Including Author, Title, Date, Pertinent Pages, etc.)</b>									
		XP-000842673 Hamaguchi, T., et al; "Novel LSI/SOI Wafer Fabrication Using Device Layer Transfer Technique" Int'l. Electron Devices Meeting, Washington, Dec. 1-4, 1985, Washington, IEEE, US, Dec. 1985, pgs. 688-691							
Examiner					Date Considered				
Sonya Marumdar					10/19/05				
Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include a copy of this form with the next communication to applicant.									